

**AMENDMENTS TO THE CLAIMS:**

Please cancel claim 19 without prejudice or disclaimer of its subject matter, and amend claims 1 and 20 as indicated below. This listing of claims will replace all prior versions and listings of claims in the application:

**LISTING OF CLAIMS:**

1. (Currently Amended) A method of manufacturing a semiconductor device, comprising:
  - forming an insulating film on a semiconductor substrate;
  - forming a groove in the insulating film;
  - filling the groove with a wiring material;
  - performing CMP to form a filled wiring layer in the groove;
  - etching the filled wiring ~~material~~ layer to thereby form a recess;
  - depositing a cap film ~~on the recess formed by etching the wiring material~~ over the semiconductor substrate;
  - performing a first polishing operation for the cap film deposited on the insulating film for removal at selectivity of R1 (= removal rate for the cap film/removal rate for the insulating film); and
  - performing a second polishing operation for the insulating film after removal of the cap film thereon at selectivity of R2 (= removal rate for the cap film/removal rate for the insulating film),

wherein each of the first polishing operation and the second polishing operation is performed by using a slurry having a condition of  $R1 > R2$ .

2. (Original) A method of manufacturing a semiconductor device according to claim 1, wherein a depth of the recess formed by etching the wiring material is larger than the thickness of the cap film.

3. (Previously Presented) A method of manufacturing a semiconductor device according to claim 1, wherein  $R1$  in the first polishing operation is equal to or larger than 1 and  $R2$  in the second polishing operation is equal to or smaller than 1.

4. (Previously Presented) A method of manufacturing a semiconductor device according to claim 1, wherein a main component of the cap film is selected from the group consisting of Ti, Ta, Nb, W, Cr, V, Pt, and Ru, a nitride, an oxide, a boride, and an alloy of any of the elements, and a mixture of the elements.

5. (Previously Presented) A method of manufacturing a semiconductor device according to claim 1, wherein a main component of the cap film is selected from the group consisting of Si, an Si oxide and an Si nitride, or the cap film is a fluorine-doped oxide film.

6. (Previously Presented) A method of manufacturing a semiconductor device according to claim 1, wherein a main component of the wiring material is selected from the group

consisting of Al, Cu, W, Ru, Ag, Mo, and Si, a nitride, an oxide, a boride and an alloy of any of the elements, and a mixture of any of the elements.

7. – 12. (Canceled)

13. (Previously Presented) A method of manufacturing a semiconductor device according to claim 2, wherein a main component of the cap film is selected from the group consisting of Ti, Ta, Nb, W, Cr, V, Pt, and Ru, a nitride, an oxide, a boride, and an alloy of any of the elements, and a mixture of the elements.

14. (Previously Presented) A method of manufacturing a semiconductor device according to claim 2, wherein a main component of the cap film is selected from the group consisting of Si, an Si oxide and an Si nitride, or the cap film is a fluorine-doped oxide film or poly-methyl-siloxane.

15. (Previously Presented) A method of manufacturing a semiconductor device according to claim 2, wherein a main component of the wiring material is selected from the group consisting of Al, Cu, W, Ru, Ag, Mo, and Si, a nitride, an oxide, a boride and an alloy of any of the elements, and a mixture of any of the elements.

16. (Previously Presented) A method of manufacturing a semiconductor device according to claim 3, wherein a main component of the cap film is selected from the group

consisting of Ti, Ta, Nb, W, Cr, V, Pt, and Ru, a nitride, an oxide, a boride, and an alloy of any of the elements, and a mixture of the elements.

17. (Previously Presented) A method of manufacturing a semiconductor device according to claim 3, wherein a main component of the cap film is selected from the group consisting of Si, an Si oxide and an Si nitride, or the cap film is a fluorine-doped oxide film or poly-methyl-siloxane.

18. (Previously Presented) A method of manufacturing a semiconductor device according to claim 3, wherein a main component of the wiring material is selected from the group consisting of Al, Cu, W, Ru, Ag, Mo, and Si, a nitride, an oxide, a boride and an alloy of any of the elements, and a mixture of any of the elements.

19. (Canceled)

20. (Currently Amended) A method of manufacturing a semiconductor device according to claim [[19]] 2, wherein the first polishing operation is performed to leave a step between the cap film in the recess and the insulating film.

21. (Previously Presented) A method of manufacturing a semiconductor device according to claim 20, wherein the second polishing operation is performed to remove the step between the cap film in the recess and the insulating film.